

General Description

The WSD45P10DN56 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

Features

- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low $R_{DS(ON)}$

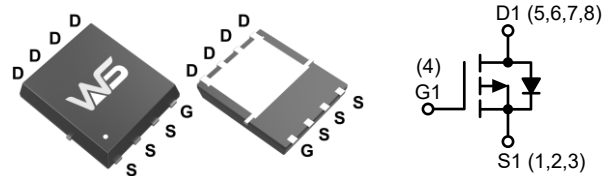
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D
-100V	62m Ω	-27.5A

Applications

- Portable equipment and battery powered systems.

DFN5X6-8L Pin Configuration



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	-100	V	
V_{GS}	Gate-Source Voltage	± 20		
I_D	Drain Current (Continuous) ³	$T_C=25^\circ\text{C}$	-27.5	A
		$T_C=100^\circ\text{C}$	-17.4	
I_{DM}	Drain Current (Pulse) ²	-110		
P_D	Power Dissipation	$T_C=25^\circ\text{C}$ 104	W	
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
T_J	Operating Junction Temperature Range	-55 to 150		

Thermal Resistance Ratings

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Maximum Junction-to-Case (Drain) ¹	Steady State ---	1.2	$^\circ\text{C/W}$

Electrical Characteristics (T_A=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-20A	---	62	81	mΩ
		V _{GS} =-6V, I _D =-15A	---	65	84.5	
		V _{GS} =-4.5V, I _D =-15A	---	70	91	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250μA	-1.0	---	-2.5	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-80V, V _{GS} =0V	---	---	1.0	μA
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Q _g	Total Gate Charge	V _{DS} =-80V, V _{GS} =-10V, I _D =-18A	---	75	---	nC
Q _{gs}	Gate-Source Charge		---	9	---	
Q _{gd}	Gate-Drain Charge		---	18	---	
T _{d(on)}	Turn-On Delay Time	V _{DS} =-50V, V _{GS} =-10V, I _D =-18A, R _G =3.3Ω	---	17	---	ns
T _r	Rise Time		---	6	---	
T _{d(off)}	Turn-Off Delay Time		---	75	---	
T _f	Fall Time		---	10	---	
C _{iss}	Input Capacitance	V _{DS} =-50V, V _{GS} =0V, f=1.0MHz	---	2590	---	pF
C _{oss}	Output Capacitance		---	320	---	
C _{rss}	Reverse Transfer Capacitance		---	45	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I _S	Diode Forward Current ³	T _C =25°C	---	---	-27.5	A
V _{SD}	Diode Forward Voltage	I _{SD} =-1A, V _{GS} =0V	---	---	-1.2	V

Note:

1. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.
2. Repetitive rating, pulse width limited by junction temperature.
3. The current rating is based on the t≤10s junction to ambient thermal resistance rating.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%.

Typical Characteristics ($T_J=25^\circ\text{C}$, Unless Otherwise Noted)

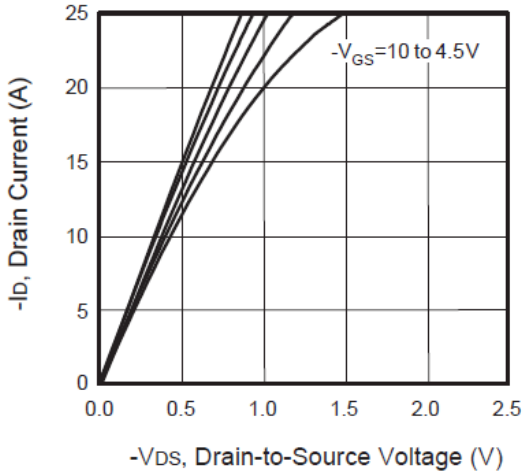


Figure 1. Output Characteristics

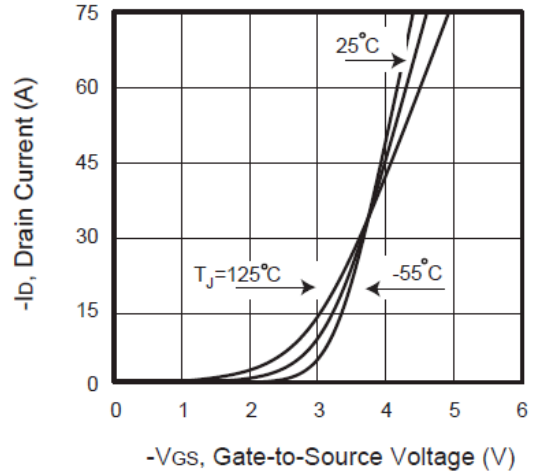


Figure 2. Transfer Characteristics

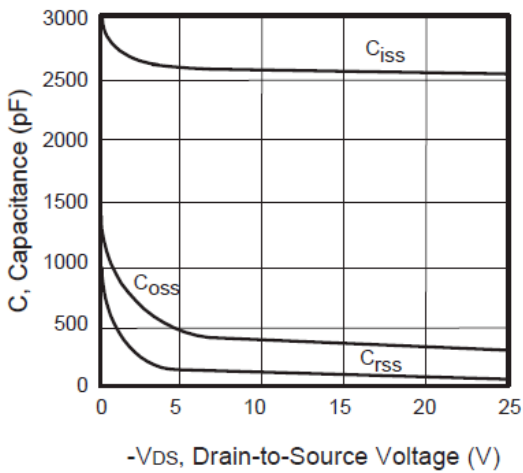


Figure 3. Capacitance

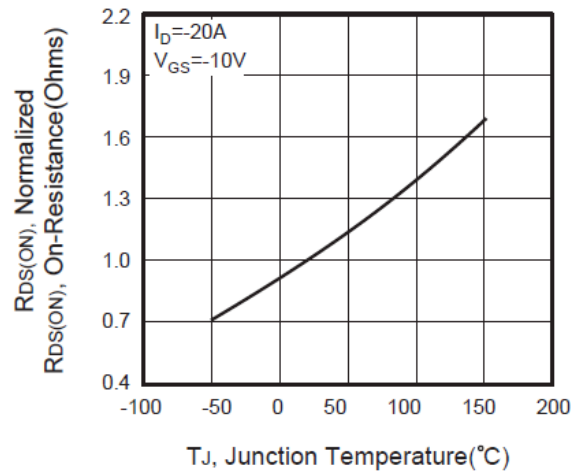


Figure 4. On-Resistance Variation with Temperature

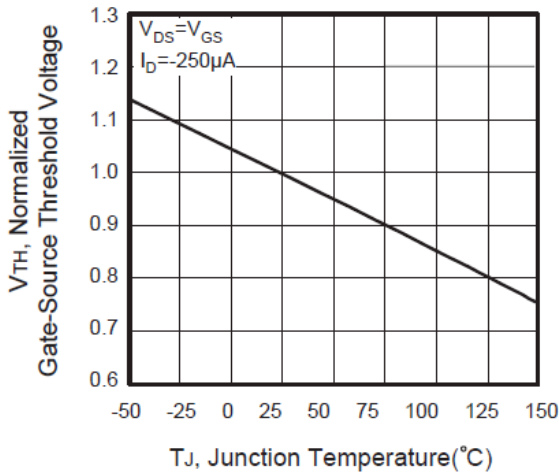


Figure 5. Gate Threshold Variation with Temperature

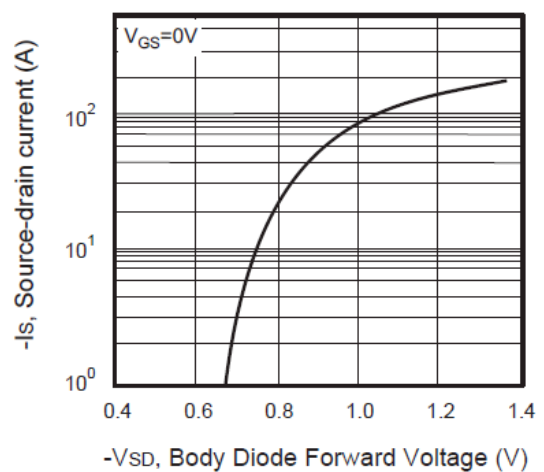


Figure 6. Body Diode Forward Voltage Variation with Source Current

Typical Characteristics (Cont.)

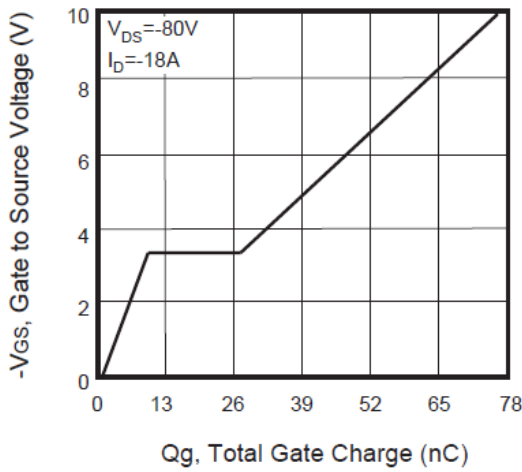


Figure 7. Gate Charge

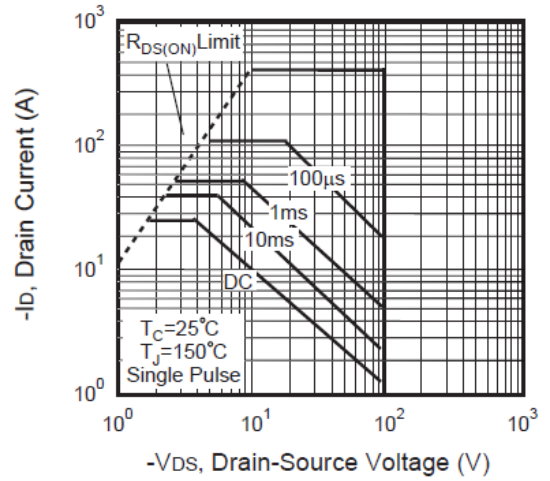


Figure 8. Maximum Safe Operating Area

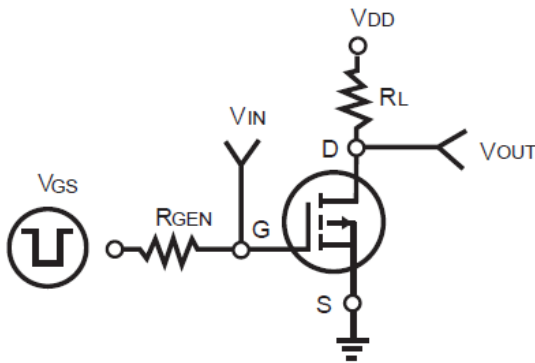


Figure 9. Switching Test Circuit

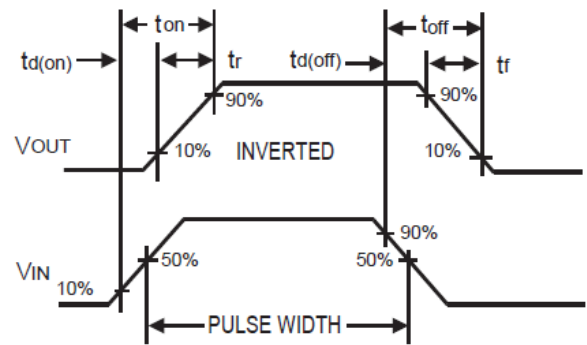


Figure 10. Switching Waveforms

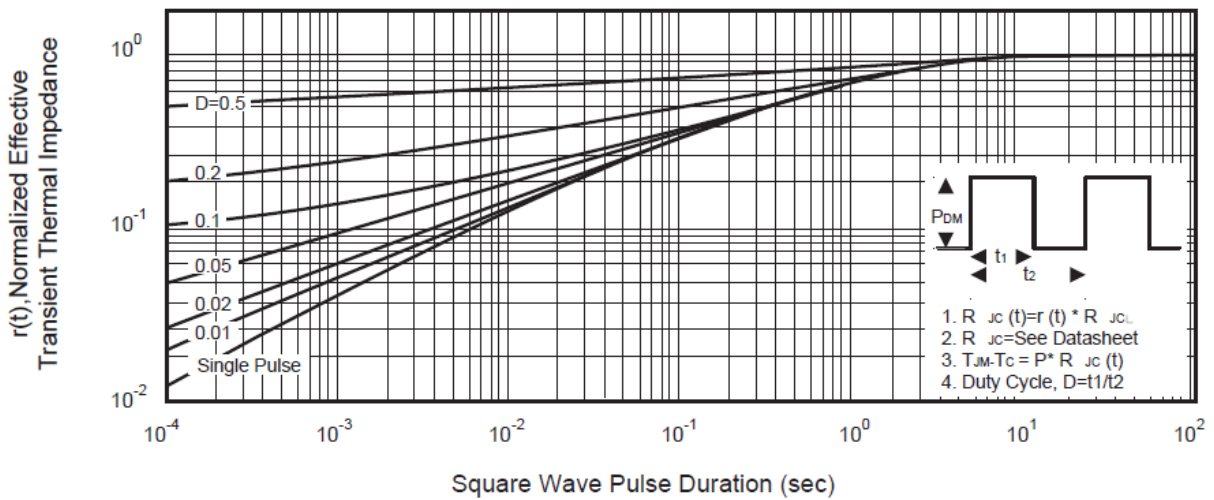
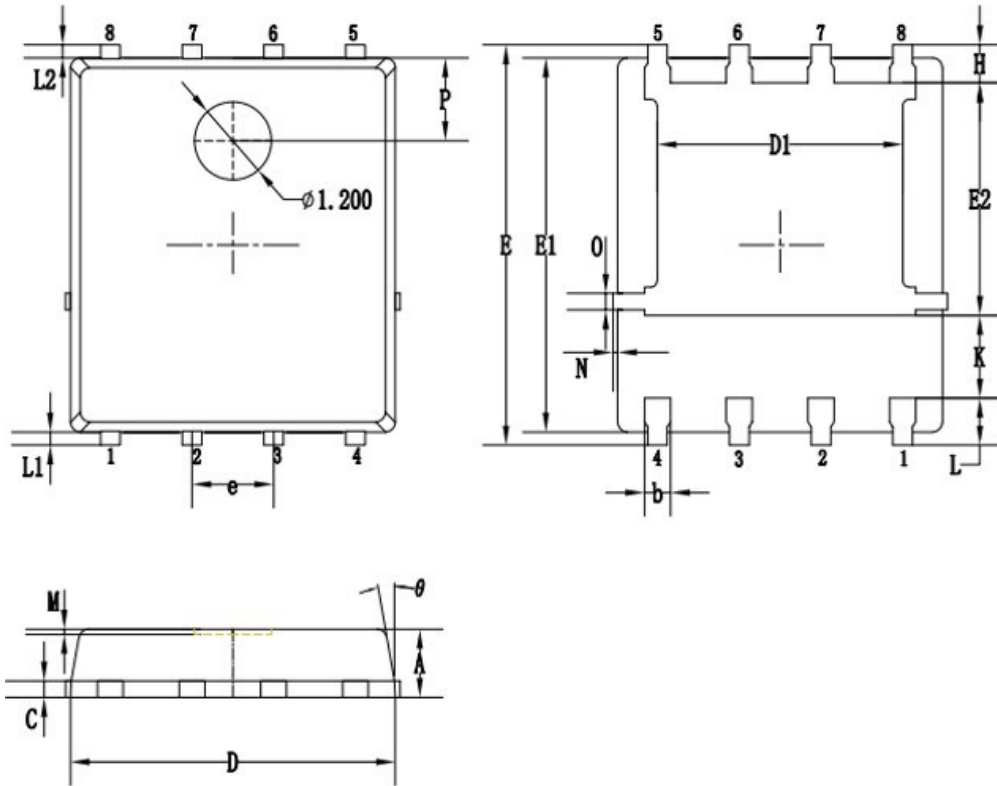


Figure 11. Normalized Thermal Transient Impedance Curve

Packaging information


SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

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